

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Original): A method of treating the surface of a material for an electronic device, comprising irradiating the surface of the material with at least a part of plasma components, while supplying a liquid to the surface of the material, to thereby flatten the surface of the material.

Claim 2 (Original): A method of treating the surface of a material for an electronic device according to claim 1, wherein the material for an electronic device is a substrate for an electronic device.

Claim 3 (Original): A method of treating the surface of a material for an electronic device according to claim 1,

wherein radicals, positive ions or negative ions based on a plasma are selectively supplied onto the surface of the material for an electronic device.

Claim 4 (Original): A method of treating the surface according to claim 1, wherein the liquid is H<sub>2</sub>O.

Claim 5 (Original): A method of treating the surface according to claim 3, wherein the radicals are high-speed neutral radicals.

Claim 6 (Withdrawn): A surface-treating apparatus, comprising at least: a processing chamber for placing a material for an electronic device to be treated at a predetermined position therein; material-holding means for holding the material for an electronic device in

the processing chamber; liquid-supplying means for supplying a liquid onto the surface of the material for an electronic device; and plasma-processing means for treating the surface of the material for an electronic device with a plasma; whereby the surface of the material can be irradiated with the plasma, while supplying the liquid onto the surface of the material for an electronic device.

Claim 7 (Withdrawn): A surface-treating apparatus according to claim 6, comprising particle selection means for selectively irradiating the surface of the material for an electronic device with at least one kind of those selected from radicals, positive ions and negative ions of the plasma components to be supplied from the plasma-processing means.

Claim 8 (New): A method of treating the surface according to claim 4, wherein said flattening is accomplished under a pressure of 10 mTorr to 1520 Torr.

Claim 9 (New): A method of treating the surface according to claim 8, wherein said flattening is accomplished under a pressure of 10 mTorr to 760 Torr.

Claim 10 (New): A method of treating the surface according to claim 9, wherein said flattening is accomplished under a pressure of about 760 Torr.

Claim 11 (New): A method of treating the surface according to claim 1, wherein said flattening is accomplished under a pressure of 10 mTorr to 1520 Torr.

Claim 12 (New): A method of treating the surface according to claim 11, wherein said flattening is accomplished under a pressure of 10 mTorr to 760 Torr.

Claim 13 (New): A method of treating the surface according to claim 11,  
wherein said flattening is accomplished under a pressure of about 760 Torr.

Claim 14 (New): A method of treating the surface according to claim 13,  
wherein said liquid is H<sub>2</sub>O.